

Matthias Schreck

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

178
papers

4,778
citations

34
h-index

61
g-index

184
ext. papers

5,194
ext. citations

3.8
avg, IF

5.12
L-index

#	Paper	IF	Citations
178	Growth of Single Crystal Diamond Wafers for Future Device Applications 2021 , 583-631		
177	Detection of x rays by a surface acoustic delay line in contact with a diamond crystal. <i>Applied Physics Letters</i> , 2021 , 118, 133501	3.4	3
176	Fe ^{II} complex emission in ZnO. <i>Journal of Applied Physics</i> , 2021 , 129, 085701	2.5	1
175	Photoconductive gain in single crystal diamond detectors. <i>Journal of Applied Physics</i> , 2021 , 129, 124502	2.5	1
174	Charge carrier trapping by dislocations in single crystal diamond. <i>Journal of Applied Physics</i> , 2020 , 127, 125102	2.5	10
173	Lift-off of single crystal diamond by epitaxial lateral overgrowth using SiO ₂ masks. <i>Diamond and Related Materials</i> , 2020 , 101, 107606	3.5	4
172	Kinetics of the Thermal Oxidation of Ir(100) toward IrO Studied by Ambient-Pressure X-ray Photoelectron Spectroscopy. <i>Journal of Physical Chemistry Letters</i> , 2020 , 11, 3601-3607	6.4	15
171	Toward wafer-scale diamond nano- and quantum technologies. <i>APL Materials</i> , 2019 , 7, 011108	5.7	21
170	Progress in detector properties of heteroepitaxial diamond grown by chemical vapor deposition on Ir/YSZ/Si(001) wafers. <i>Diamond and Related Materials</i> , 2019 , 97, 107420	3.5	12
169	Polarization-sensitive reconstruction of transient local THz fields at dielectric interfaces. <i>Optica</i> , 2019 , 6, 1431	8.6	0
168	Centimeter-Sized Single-Orientation Monolayer Hexagonal Boron Nitride With or Without Nanovoids. <i>Nano Letters</i> , 2018 , 18, 1205-1212	11.5	34
167	Growth, stress, and defects of heteroepitaxial diamond on Ir/YSZ/Si(111). <i>Journal of Applied Physics</i> , 2018 , 123, 225302	2.5	17
166	Microstructural Effect on the Enhancement of Field Electron Emission Properties of Nanocrystalline Diamond Films by Li-Ion Implantation and Annealing Processes. <i>ACS Omega</i> , 2018 , 3, 9956-9965	3.9	6
165	Pulse-resolved intensity measurements at a hard X-ray FEL using semi-transparent diamond detectors. <i>Journal of Synchrotron Radiation</i> , 2018 , 25, 177-188	2.4	9
164	Epitaxial Growth of Graphene on Single-Crystal Cu(111) Wafers 2018 , 97-106		1
163	Propagation of threading dislocations in heteroepitaxial diamond films with (111) orientation and their role in the formation of intrinsic stress. <i>Journal of Applied Physics</i> , 2017 , 121, 225301	2.5	9
162	Ion bombardment induced buried lateral growth: the key mechanism for the synthesis of single crystal diamond wafers. <i>Scientific Reports</i> , 2017 , 7, 44462	4.9	95

161	Characterization of CVD Heavily B-Doped Diamond Thin Films for Multi Electrode Array Biosensors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1700223	1.6	5
160	Fermi surface map of large-scale single-orientation graphene on SiO. <i>Journal of Physics Condensed Matter</i> , 2017 , 29, 475001	1.8	5
159	Single Crystalline Metal Films as Substrates for Graphene Growth. <i>Annalen Der Physik</i> , 2017 , 529, 17000286		4
158	Field electron emission enhancement in lithium implanted and annealed nitrogen-incorporated nanocrystalline diamond films. <i>Applied Physics Letters</i> , 2017 , 110, 261602	3.4	11
157	Controlled thermodynamics for tunable electron doping of graphene on Ir(111). <i>Physical Review B</i> , 2016 , 94,	3.3	4
156	Multiple role of dislocations in the heteroepitaxial growth of diamond: A brief review. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 2028-2035	1.6	19
155	Propagation and annihilation of threading dislocations during off-axis growth of heteroepitaxial diamond films. <i>Diamond and Related Materials</i> , 2016 , 65, 53-58	3.5	20
154	Localization of Narrowband Single Photon Emitters in Nanodiamonds. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 7590-4	9.5	10
153	Direct imaging of boron segregation at dislocations in B:diamond heteroepitaxial films. <i>Nanoscale</i> , 2016 , 8, 2212-8	7.7	16
152	Detachment of CVD-grown graphene from single crystalline Ni films by a pure gas phase reaction. <i>Surface Science</i> , 2016 , 653, 143-152	1.8	13
151	Production yield of rare-earth ions implanted into an optical crystal. <i>Applied Physics Letters</i> , 2016 , 108, 053108	3.4	16
150	Site selective growth of heteroepitaxial diamond nanoislands containing single SiV centers. <i>Applied Physics Letters</i> , 2016 , 108, 063111	3.4	16
149	Formation of huge in-plane anisotropy of intrinsic stress by off-axis growth of diamond. <i>Applied Physics Letters</i> , 2016 , 109, 141907	3.4	5
148	Magnetic Nano-skyrmion Lattice Observed in a Si-Wafer-Based Multilayer System. <i>ACS Nano</i> , 2015 , 9, 5908-12	16.7	17
147	High-quality graphene on single crystal Ir(1 1 1) films on Si(1 1 1) wafers: Synthesis and multi-spectroscopic characterization. <i>Carbon</i> , 2015 , 81, 167-173	10.4	11
146	Interaction between surface structures and threading dislocations during epitaxial diamond growth. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 2480-2486	1.6	7
145	Graphene/Silicon Layered Structures on Single-Crystalline Ir(111) Thin Films. <i>Advanced Materials Interfaces</i> , 2015 , 2, 1400543	4.6	11
144	Optical signatures of silicon-vacancy spins in diamond. <i>Nature Communications</i> , 2014 , 5, 3328	17.4	121

143	Correlation between surface morphology and defect structure of heteroepitaxial diamond grown on off-axis substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 2257-2263	1.6	14
142	Mutual interaction of N, B, and O during heteroepitaxial diamond growth: Triggering the nitrogen induced growth acceleration. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 2290-2295	1.6	4
141	Deterministic coupling of a single silicon-vacancy color center to a photonic crystal cavity in diamond. <i>Nano Letters</i> , 2014 , 14, 5281-7	11.5	106
140	Large-area high-quality single crystal diamond. <i>MRS Bulletin</i> , 2014 , 39, 504-510	3.2	75
139	Graphene from fingerprints: exhausting the performance of liquid precursor deposition. <i>Langmuir</i> , 2014 , 30, 6114-9	4	5
138	The first prototype diamond monochromator at the Institut Laue-Langevin. <i>Journal of Physics: Conference Series</i> , 2014 , 528, 012001	0.3	2
137	Tuned NV emission by in-plane Al-Schottky junctions on hydrogen terminated diamond. <i>Scientific Reports</i> , 2014 , 4, 3634	4.9	31
136	Healing of graphene on single crystalline Ni(111) films. <i>Applied Physics Letters</i> , 2014 , 105, 191612	3.4	13
135	Single Crystal Diamond Growth on Iridium 2014 , 269-304		4
134	High quality single atomic layer deposition of hexagonal boron nitride on single crystalline Rh(111) four-inch wafers. <i>Review of Scientific Instruments</i> , 2014 , 85, 035101	1.7	45
133	Yttria-stabilized zirconia buffered silicon to optimize in-plane electrical conductivity of [Ca ₂ CoO ₃] _{0.62} [CoO ₂] thin films. <i>Applied Physics Letters</i> , 2014 , 104, 183104	3.4	7
132	Low-temperature investigations of single silicon vacancy colour centres in diamond. <i>New Journal of Physics</i> , 2013 , 15, 043005	2.9	106
131	Increasing the wear resistance by interstitial alloying with boron via chemical vapor deposition. <i>Langmuir</i> , 2013 , 29, 4543-50	4	3
130	Efficiency of dislocation density reduction during heteroepitaxial growth of diamond for detector applications. <i>Applied Physics Letters</i> , 2013 , 103, 151905	3.4	45
129	Structural analysis of diamond mosaic crystals for neutron monochromators using synchrotron radiation. <i>Diamond and Related Materials</i> , 2013 , 37, 41-49	3.5	7
128	Exchange bias in reduced dimensions: Cobalt nanocluster arrays under the influence of nanometer thin MnPt capping layers. <i>Journal of Applied Physics</i> , 2013 , 113, 123903	2.5	7
127	Epitaxial growth of europium monoxide on diamond. <i>Applied Physics Letters</i> , 2013 , 103, 222402	3.4	7
126	Synthesis and characterization of peapods and DWCNTs. <i>Physica Status Solidi (B): Basic Research</i> , 2012 , 249, 2345-2348	1.3	8

125	Scalable synthesis of graphene on single crystal Ir(111) films. <i>Surface Science</i> , 2012 , 606, 1475-1480	1.8	28
124	In situ boron doping during heteroepitaxial growth of diamond on Ir/YSZ/Si. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 1643-1650	1.6	14
123	Electronic transitions of single silicon vacancy centers in the near-infrared spectral region. <i>Physical Review B</i> , 2012 , 85,	3.3	28
122	Epitaxial growth of graphene on transition metal surfaces: chemical vapor deposition versus liquid phase deposition. <i>Journal of Physics Condensed Matter</i> , 2012 , 24, 314204	1.8	30
121	Growth sector dependence and mechanism of stress formation in epitaxial diamond growth. <i>Applied Physics Letters</i> , 2012 , 100, 041906	3.4	17
120	One- and two-dimensional photonic crystal microcavities in single crystal diamond. <i>Nature Nanotechnology</i> , 2011 , 7, 69-74	28.7	192
119	Single photon emission from silicon-vacancy colour centres in chemical vapour deposition nano-diamonds on iridium. <i>New Journal of Physics</i> , 2011 , 13, 025012	2.9	297
118	Diamond mosaic crystals for neutron instrumentation: First experimental results. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2011 , 634, S28-S36	1.2	8
117	Fluorescence and polarization spectroscopy of single silicon vacancy centers in heteroepitaxial nanodiamonds on iridium. <i>Physical Review B</i> , 2011 , 84,	3.3	62
116	Epitaxial growth of graphene on Ir(111) by liquid precursor deposition. <i>Physical Review B</i> , 2011 , 84,	3.3	21
115	Multimode photoacoustic method for the evaluation of mechanical properties of heteroepitaxial diamond layers. <i>Journal of Applied Physics</i> , 2010 , 108, 083524	2.5	14
114	Reentrant superconductivity in superconductor/ferromagnetic-alloy bilayers. <i>Physical Review B</i> , 2010 , 82,	3.3	38
113	STM, SECPM, AFM and Electrochemistry on Single Crystalline Surfaces. <i>Materials</i> , 2010 , 3, 4196-4213	3.5	17
112	Thermal diffusivity of heteroepitaxial diamond films: Experimental setup and measurements. <i>Diamond and Related Materials</i> , 2010 , 19, 787-791	3.5	4
111	Epitaxial growth of hexagonal boron nitride monolayers by a three-step boration-oxidation-nitration process. <i>Physical Review B</i> , 2010 , 82,	3.3	33
110	Diamond detectors for hadron physics research. <i>Diamond and Related Materials</i> , 2010 , 19, 358-367	3.5	45
109	Supramolecular Assemblies Formed on an Epitaxial Graphene Superstructure. <i>Angewandte Chemie</i> , 2010 , 122, 1838-1843	3.6	11
108	Supramolecular assemblies formed on an epitaxial graphene superstructure. <i>Angewandte Chemie - International Edition</i> , 2010 , 49, 1794-9	16.4	104

107	Comparison of diamond bias enhanced nucleation on Ir and 3C-SiC: A high resolution electron energy loss spectroscopy study. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1972-1977	1.6	7
106	How does graphene grow? Easy access to well-ordered graphene films. <i>Small</i> , 2009 , 5, 2291-6	11	39
105	Quasi-one-dimensional Fulde-Ferrell-Larkin-Ovchinnikov-like state in Nb/Cu _{0.41} Ni _{0.59} bilayers. <i>JETP Letters</i> , 2009 , 90, 139-142	1.2	11
104	Epitaxial films of metals from the platinum group (Ir, Rh, Pt and Ru) on YSZ-buffered Si(1 1 1). <i>Journal of Crystal Growth</i> , 2009 , 311, 3731-3736	1.6	51
103	Growth rate enhancement by nitrogen in diamond chemical vapor deposition – catalytic effect. <i>Applied Physics Letters</i> , 2009 , 94, 224101	3.4	39
102	Diamond nucleation on iridium: Local variations of structure and density within the BEN layer. <i>Diamond and Related Materials</i> , 2009 , 18, 107-112	3.5	11
101	Double re-entrance of superconductivity in superconductor/ferromagnet bilayers. <i>Journal of Physics: Conference Series</i> , 2009 , 150, 052242	0.3	4
100	Heteroepitaxial Growth 2009 , 125-161		6
99	ZnO Nanostructures: Optical Resonators and Lasing. <i>Advances in Solid State Physics</i> , 2009 , 39-56		2
98	Extinction and Recovery of Superconductivity by Interference in Superconductor/Ferromagnet Bilayers. <i>Nanoscience and Technology</i> , 2009 , 3-11	0.6	3
97	Preparation of 4-inch Ir/YSZ/Si(001) substrates for the large-area deposition of single-crystal diamond. <i>Diamond and Related Materials</i> , 2008 , 17, 1035-1038	3.5	48
96	Comparative electron diffraction study of the diamond nucleation layer on Ir(001). <i>Diamond and Related Materials</i> , 2008 , 17, 1029-1034	3.5	19
95	Transmission electron microscopy study of the very early stages of diamond growth on iridium. <i>Diamond and Related Materials</i> , 2008 , 17, 1045-1050	3.5	29
94	Iridium on Biaxially Textured Oxide Templates: A Concept to Grow Single Crystals on Arbitrary Substrates. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 8925-8927	1.4	10
93	Growth of twin-free heteroepitaxial diamond on Ir/YSZ/Si(111). <i>Journal of Applied Physics</i> , 2008 , 104, 123531	2.5	20
92	Reduction of mosaic spread using iridium interlayers: A route to improved oxide heteroepitaxy on silicon. <i>Applied Physics Letters</i> , 2007 , 91, 061501	3.4	29
91	Combined AFM/SEM study of the diamond nucleation layer on Ir(001). <i>Diamond and Related Materials</i> , 2007 , 16, 665-670	3.5	15
90	Boron nitride nanomesh: functionality from a corrugated monolayer. <i>Angewandte Chemie - International Edition</i> , 2007 , 46, 5115-9	16.4	196

89	Boron Nitride Nanomesh: Functionality from a Corrugated Monolayer. <i>Angewandte Chemie</i> , 2007 , 119, 5207-5211	3.6	20
88	Afterglow and thermally stimulated luminescence induced by UV radiation in CVD diamond. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 3047-3052	1.6	7
87	Growth of zinc oxide nanopillars on an iridium/yttria-stabilized zirconia/silicon substrate. <i>Applied Physics Letters</i> , 2007 , 90, 233115	3.4	9
86	Interaction of small diamond islands on iridium: A finite element simulation study. <i>Diamond and Related Materials</i> , 2007 , 16, 705-710	3.5	3
85	Epitaxial lateral overgrowth (ELO) of homoepitaxial diamond through an iridium mesh. <i>Diamond and Related Materials</i> , 2007 , 16, 711-717	3.5	14
84	Structural Properties of the Diamond Nucleation Layer on Iridium Analyzed by Laterally Resolved X-Ray Absorption Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, L984-L986	1.4	11
83	Performance of CVD diamond as an optically and thermally stimulated luminescence dosimeter. <i>Radiation Protection Dosimetry</i> , 2006 , 119, 226-9	0.9	3
82	Reentrant superconductivity in Nb/Cu _{1-x} Ni _x bilayers. <i>Physical Review Letters</i> , 2006 , 97, 057004	7.4	101
81	Yttria-stabilized zirconia films of different composition as buffer layers for the deposition of epitaxial diamond/Ir layers on Si(001). <i>Diamond and Related Materials</i> , 2006 , 15, 479-485	3.5	21
80	Homoepitaxial diamond layers on off-axis Ib HPHT substrates: Growth of thick films and characterisation by high-resolution X-ray diffraction. <i>Diamond and Related Materials</i> , 2006 , 15, 472-478	3.5	24
79	Transmission electron microscopy study of the diamond nucleation layer on iridium. <i>Diamond and Related Materials</i> , 2006 , 15, 460-464	3.5	21
78	Comparison of MWPCVD diamond growth at low and high process gas pressures. <i>Diamond and Related Materials</i> , 2006 , 15, 542-547	3.5	28
77	Structural defects in homoepitaxial diamond layers grown on off-axis Ib HPHT substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 3056-3062	1.6	23
76	Afterglow, TL and IRSL in beta-irradiated HPHT type Ib synthetic diamond. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 3167-3172	1.6	3
75	All optical read-out radiation dosimeter using CVD synthetic diamond. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 3173-3178	1.6	4
74	The nucleation centers formed during bias-enhanced nucleation of diamond on iridium: structure and stability. <i>Diamond and Related Materials</i> , 2005 , 14, 328-334	3.5	6
73	Growth of epitaxial diamond on silicon via iridium/SrTiO ₃ buffer layers. <i>Diamond and Related Materials</i> , 2005 , 14, 314-317	3.5	35
72	High growth rate homoepitaxial diamond deposition on off-axis substrates. <i>Diamond and Related Materials</i> , 2005 , 14, 266-271	3.5	58

71	Extended defect related energy loss in CVD diamond revealed by spectrum imaging in a dedicated STEM. <i>Ultramicroscopy</i> , 2005 , 104, 46-56	3.1	8
70	Thermoluminescence characterization of a MWCVD diamond film exposed to γ rays and UV radiation. <i>Physica Status Solidi A</i> , 2005 , 202, 2206-2211		10
69	Joint density of states at extended defects in CVD diamond, observed via highly spatially resolved electron energy loss spectroscopy. <i>Physica Status Solidi A</i> , 2005 , 202, 2188-2193		3
68	Crystal tilting of diamond heteroepitaxially grown on vicinal IrBrTiO ₃ (001). <i>Journal of Applied Physics</i> , 2004 , 96, 1413-1417	2.5	7
67	Diamond-based electronics for RF applications. <i>Diamond and Related Materials</i> , 2004 , 13, 233-240	3.5	29
66	Growth mechanism for epitaxial cubic boron nitride films on diamond substrates by ion beam assisted deposition. <i>Diamond and Related Materials</i> , 2004 , 13, 1144-1148	3.5	18
65	Surface modifications and first stages of heteroepitaxial diamond growth on iridium. <i>Diamond and Related Materials</i> , 2004 , 13, 335-341	3.5	17
64	A route to diamond wafers by epitaxial deposition on silicon via iridium/yttria-stabilized zirconia buffer layers. <i>Applied Physics Letters</i> , 2004 , 84, 4541-4543	3.4	94
63	Dislocation-induced electronic states and point-defect atmospheres evidenced by electron energy loss imaging. <i>New Journal of Physics</i> , 2004 , 6, 184-184	2.9	11
62	Oscillations of the critical temperature in superconducting Nb/Ni bilayers. <i>Annalen Der Physik</i> , 2003 , 12, 37-50	2.6	58
61	Epitaxial rhenium buffer layers on Al ₂ O ₃ (0001): a substrate for the deposition of (111)-oriented heteroepitaxial diamond films. <i>Physica Status Solidi A</i> , 2003 , 199, 19-26		16
60	Epitaxy of cubic boron nitride on (001)-oriented diamond. <i>Nature Materials</i> , 2003 , 2, 312-5	2.7	118
59	Domain formation in diamond nucleation on iridium. <i>Diamond and Related Materials</i> , 2003 , 12, 262-267	3.5	36
58	Field effect transistor fabricated on hydrogen-terminated diamond grown on SrTiO ₃ substrate and iridium buffer layer. <i>Diamond and Related Materials</i> , 2003 , 12, 403-407	3.5	22
57	TEM analysis of nanometer-size surface structures formed by bias enhanced nucleation of diamond on iridium. <i>Diamond and Related Materials</i> , 2003 , 12, 350-355	3.5	10
56	Diamond field effect transistors—concepts and challenges. <i>Diamond and Related Materials</i> , 2003 , 12, 391-398	3.5	87
55	Optical and structural analysis of ZnCdO layers grown by metalorganic vapor-phase epitaxy. <i>Applied Physics Letters</i> , 2003 , 83, 3290-3292	3.4	165
54	Growth and properties of CVD diamond films grown under H ₂ S addition. <i>Diamond and Related Materials</i> , 2003 , 12, 318-323	3.5	21

53	Orientation dependent sputter yield of aluminium. <i>Surface and Coatings Technology</i> , 2002 , 151-152, 72-74	4	18
52	Flat epitaxial diamond/Ir(001) interface visualized by high resolution transmission electron microscopy. <i>Surface Science</i> , 2002 , 513, 525-529	1.8	11
51	Mosaicity reduction during growth of heteroepitaxial diamond films on iridium buffer layers: Experimental results and numerical simulations. <i>Journal of Applied Physics</i> , 2002 , 91, 676-685	2.5	48
50	In situ characterisation of CVD diamond growth under H ₂ S addition by optical emission spectroscopy, mass spectroscopy and laser reflection interferometry. <i>Diamond and Related Materials</i> , 2002 , 11, 296-300	3.5	17
49	Analysis of the total carbon deposition during the bias enhanced nucleation of diamond on Ir/SrTiO ₃ (001) using ¹³ C-methane. <i>Diamond and Related Materials</i> , 2002 , 11, 493-498	3.5	20
48	Bias assisted growth on diamond single crystals: the defect formation due to ion bombardment studied by ion channelling, electron backscatter diffraction, and micro-Raman spectroscopy. <i>Diamond and Related Materials</i> , 2002 , 11, 487-492	3.5	9
47	Diamond nucleation on iridium buffer layers and subsequent textured growth: A route for the realization of single-crystal diamond films. <i>Applied Physics Letters</i> , 2001 , 78, 192-194	3.4	98
46	Dispersion of surface acoustic waves in polycrystalline diamond plates. <i>Diamond and Related Materials</i> , 2001 , 10, 686-692	3.5	28
45	First stages of diamond nucleation on iridium buffer layers. <i>Diamond and Related Materials</i> , 2001 , 10, 1617-1621	3.5	32
44	Photoconductivity Study of Li Doped Homoepitaxially Grown CVD Diamond. <i>Physica Status Solidi A</i> , 2000 , 181, 45-50		16
43	Raman study of titanium oxide layers produced with plasma immersion ion implantation. <i>Surface and Coatings Technology</i> , 2000 , 125, 84-88	4.4	52
42	Damage buildup and removal in Ca-ion-implanted GaN. <i>Applied Physics A: Materials Science and Processing</i> , 2000 , 70, 53-57	2.6	8
41	Field emission mechanism from undoped chemical vapor deposition diamond films. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000 , 18, 1031		11
40	Stress distribution in thin heteroepitaxial diamond films on Ir/SrTiO ₃ studied by x-ray diffraction, Raman spectroscopy, and finite element simulations. <i>Journal of Applied Physics</i> , 2000 , 88, 2456-2466	2.5	24
39	Epitaxial Ir layers on SrTiO ₃ as substrates for diamond nucleation: deposition of the films and modification in the CVD environment. <i>Diamond and Related Materials</i> , 2000 , 9, 256-261	3.5	32
38	Lithium addition during CVD diamond growth: influence on the optical emission of the plasma and properties of the films. <i>Diamond and Related Materials</i> , 2000 , 9, 1046-1050	3.5	21
37	Control of Lithium-t-Butoxide Addition during Chemical Vapour Deposition of Li-Doped Diamond Films by Optical Emission Spectroscopy. <i>Physica Status Solidi A</i> , 1999 , 174, 65-72		7
36	Diamond/Ir/SrTiO ₃ : A material combination for improved heteroepitaxial diamond films. <i>Applied Physics Letters</i> , 1999 , 74, 650-652	3.4	107

35	Effect of oxygen on the bias-enhanced nucleation of diamond on silicon. <i>Diamond and Related Materials</i> , 1999 , 8, 160-165	3.5	6
34	Oxygen at the interface of CVD diamond films on silicon. <i>Diamond and Related Materials</i> , 1999 , 8, 1142-1147	3.5	7
33	Influence of structural and morphological properties on the intrinsic field emission of CVD diamond films. <i>Diamond and Related Materials</i> , 1998 , 7, 666-670	3.5	13
32	Incorporation of nitrogen into carbon films produced by PECVD under bias voltage. <i>Diamond and Related Materials</i> , 1998 , 7, 899-902	3.5	12
31	Modification of diamond film growth by a negative bias voltage in microwave plasma chemical vapor deposition. <i>Diamond and Related Materials</i> , 1998 , 7, 293-298	3.5	20
30	Bias Enhanced Nucleation and Growth of Diamond Films on Titanium Substrates. <i>Materials Science Forum</i> , 1998 , 287-288, 315-318	0.4	
29	Modifying chemical vapor deposited diamond films for field emission displays. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998 , 16, 693		15
28	Limiting processes for diamond epitaxial alignment on silicon. <i>Physical Review B</i> , 1998 , 57, 15454-15464	3.3	39
27	Limitations of the process window for the bias enhanced nucleation of heteroepitaxial diamond films on silicon in the time domain. <i>Journal of Applied Physics</i> , 1997 , 81, 3092-3095	2.5	24
26	Influence of the nucleation process on the azimuthal misorientation of heteroepitaxial diamond films on Si(001). <i>Journal of Applied Physics</i> , 1997 , 81, 3096-3102	2.5	25
25	Electron beam-induced current imaging of chemical vapor-deposited diamond films. <i>Diamond and Related Materials</i> , 1997 , 6, 95-98	3.5	5
24	Growth and defects of diamond facets under negative biasing conditions in a microwave plasma CVD process. <i>Diamond and Related Materials</i> , 1997 , 6, 1010-1014	3.5	5
23	TEM investigations on the heteroepitaxial nucleation of CVD diamond on (001) silicon substrates. <i>Diamond and Related Materials</i> , 1997 , 6, 752-757	3.5	20
22	AFM study on the non-monotonic texture evolution of heteroepitaxially nucleated diamond films. <i>Diamond and Related Materials</i> , 1996 , 5, 266-271	3.5	
21	Deposition of heteroepitaxial diamond films on 2 in silicon substrates. <i>Diamond and Related Materials</i> , 1996 , 5, 251-255	3.5	22
20	Nucleation and Growth of Heteroepitaxial Diamond Films on Silicon. <i>Physica Status Solidi A</i> , 1996 , 154, 197-217		51
19	Study of the Growth of Thin Expitaxial CVD Diamond Films on Silicon. <i>Materials Science Forum</i> , 1996 , 228-231, 445-450	0.4	0
18	Study of the initial growth phase of chemical vapor deposited diamond on silicon(001) by synchrotron radiation. <i>Journal of Applied Physics</i> , 1996 , 79, 1907-1910	2.5	7

17	X-ray imaging of polycrystalline materials). <i>Review of Scientific Instruments</i> , 1995 , 66, 3560-3562	1.7	26
16	Optical characterization of the cathode plasma sheath during the biasing step for diamond nucleation on silicon. <i>Diamond and Related Materials</i> , 1995 , 4, 553-558	3.5	32
15	Texture analysis of chemical vapor deposited diamond films on silicon by the component method. <i>Journal of Applied Physics</i> , 1995 , 77, 4765-4770	2.5	7
14	Indications of non-monotonic texture evolution from a two-dimensional simulation study. <i>Diamond and Related Materials</i> , 1995 , 4, 416-418	3.5	7
13	The influence of the growth process on the film texture of epitaxially nucleated diamond on silicon (001). <i>Diamond and Related Materials</i> , 1995 , 4, 410-415	3.5	28
12	High Field Electrical Conductivity and Breakdown in Heteroepitaxial Diamond Films. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 416, 337		1
11	Characterization of the near-interface region of chemical vapor deposited diamond films on silicon by backscatter Kikuchi diffraction. <i>Applied Physics Letters</i> , 1994 , 65, 1781-1783	3.4	10
10	Correlation between breakdown voltage and structural properties of polycrystalline and heteroepitaxial CVD diamond films. <i>Diamond and Related Materials</i> , 1994 , 3, 951-956	3.5	21
9	Structural characterization of diamond films grown epitaxially on silicon. <i>Diamond and Related Materials</i> , 1994 , 3, 510-514	3.5	51
8	Interaction of slow electrons with organic films: theoretical and experimental HREELS studies on selectively deuterated molecules. <i>Surface Science</i> , 1992 , 262, 128-140	1.8	10
7	Comparative optical reflection and mass spectrometry analysis of thermodesorption of Langmuir-Blodgett films. <i>Thin Solid Films</i> , 1992 , 213, 136-142	2.2	8
6	Preparation and spectroscopic characterization of a thin polymer film in ultra high vacuum: 2,5-distyrylpyrazine. <i>Journal of Chemical Physics</i> , 1991 , 94, 3235-3241	3.9	4
5	Thermodesorption of Langmuir-Blodgett films studied by mass spectrometry. <i>Langmuir</i> , 1991 , 7, 2287-2292		7
4	HREELS-studies of selectively deuterated cadmium-stearate Langmuir-Blodgett films. <i>Surface Science</i> , 1990 , 237, L405-L410	1.8	18
3	Epitaxial growth of thin films of perylenetetracar?ylic dianhydride and coronene on NaCl(001). <i>Thin Solid Films</i> , 1989 , 175, 89-93	2.2	32
2	Interaction of metals with cadmium arachidate Langmuir-Blodgett films studied by X-ray photoelectron spectroscopy. <i>Thin Solid Films</i> , 1989 , 175, 95-101	2.2	19
1	First diamond FET RF power measurement on diamond quasi-substrate		5